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CORRECTION

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Correction: Solvent-free vacuum growth of oriented HKUST-1 thin films

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Correction for 'Solvent-free vacuum growth of oriented HKUST-1 thin films' by Sungmin Han *et al.*, *J. Mater. Chem. A*, 2019, **7**, 19396–19406.

The authors regret a labelling error in Fig. 4(b); a peak labelled '300' in the published article should instead have been labelled '400'. Moreover, on page 19401, the phrase '(200) and (300) planes' should instead have read '(200) and (400) planes'.

A corrected version of Fig. 4 can be found below.

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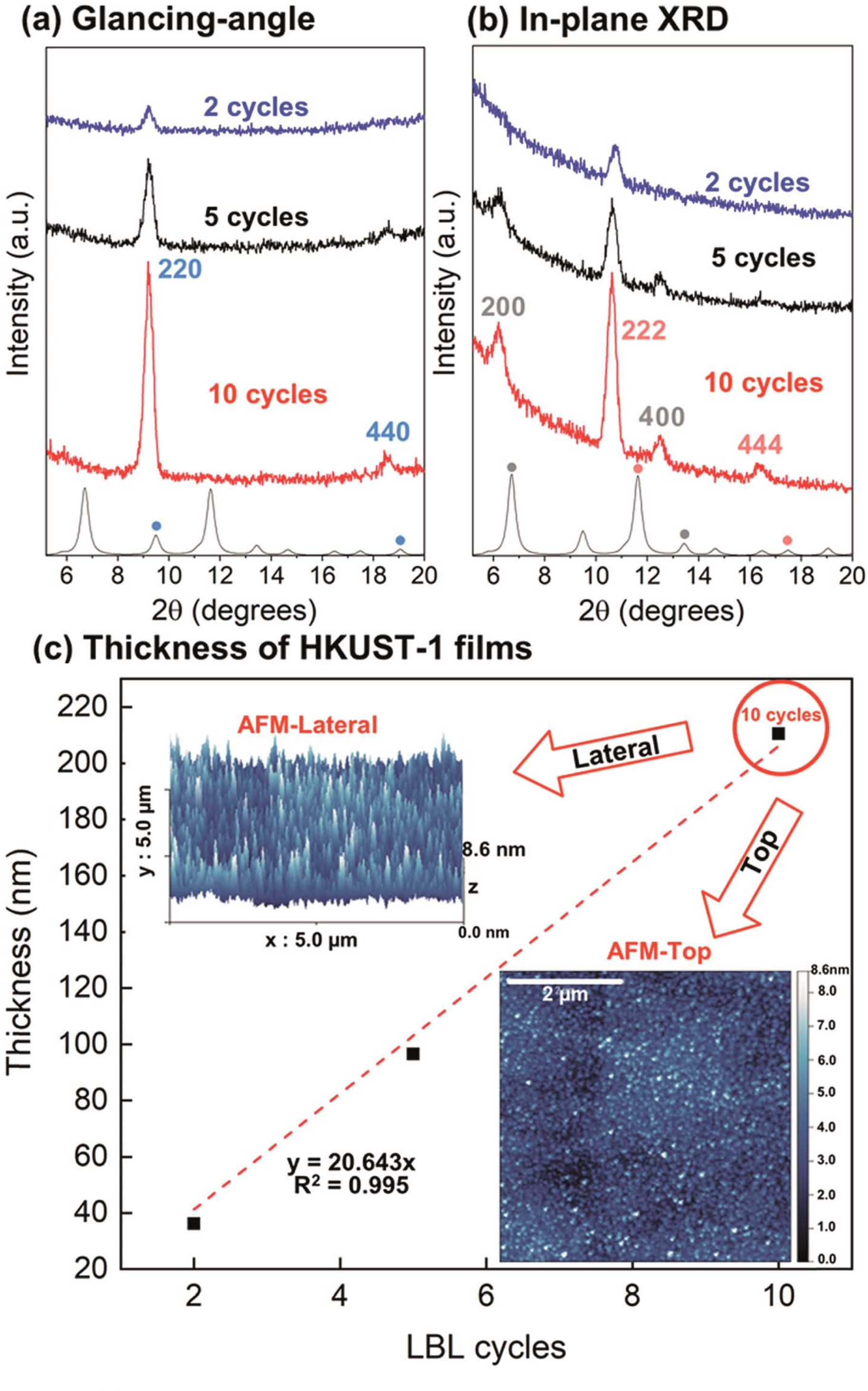

Fig. 4 (a) The glancing-angle and (b) the in-plane XRD measurements for 2, 5, 10 LBL cycles of HKUST-1 thin films with simulated HKUST-1 XRD patterns (black lines at the bottom of each figure). (c) shows the thickness of these HKUST-1 thin films measured by AFM. Top and lateral views of the 10 cycled HKUST-1 film are also included as insets.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.